



晶体管 TRANSISTOR S8050DAF

主要参数 MAIN CHARACTERISTICS

I _c	1.5A
V _{CEO}	45V
P _c	625mW

产品特性 FEATURES

硅外延	Epitaxial silicon
高开关速度	High switching speed
与 S8550A 互补	Complementary to S8550A
RoHS 产品	RoHS product

用途 APPLICATIONS

高频开关电源	High frequency switch power supply
一般功率放大电路	Commonly power amplifier circuit
高频功率变换	High frequency power transform

封装形式 Package



TO-92

1. Emitter 2. Collector 3. Base

绝对最大额定值 ABSOLUTE RATINGS (T_c=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
集电极—基极直流电压 Collector- Base Voltage (I _E =0)	V _{CB0}	120	V
集电极—发射极直流电压 Collector- Emitter Voltage (I _B =0)	V _{CEO}	45	V
发射极—基极直流电压 Emitter-Base Voltage (I _C =0)	V _{EB0}	7	V
最大集电极直流电流 Collector Current (DC)	I _c	1.5	A
最大集电极耗散功率 Total Dissipation (TO-92)	P _c	1	W
最高结温 Junction Temperature	T _j	150	°C
贮存温度 Storage Temperature	T _{stg}	-55~+150	°C

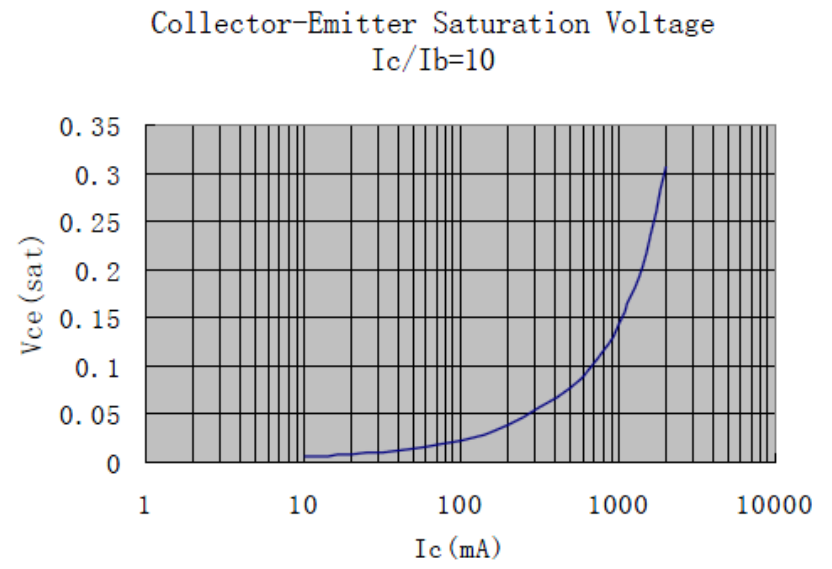
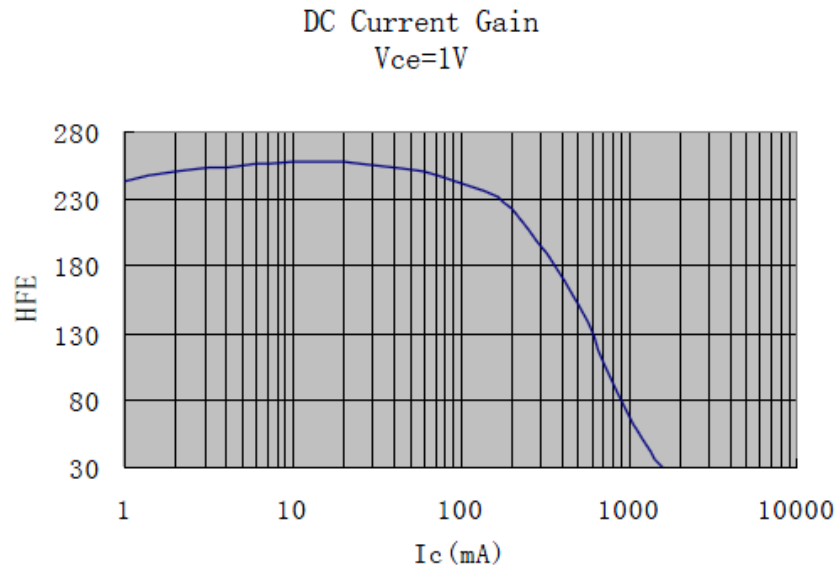
电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	测试条件 Tests conditions	最小值 (min)	典型值 (typ)	最大值 (max)	单位 Unit
V(BR) _{CBO}	I _C =0.1mA, I _E =0	120	-	-	V
V(BR) _{CEO}	I _C =2mA, I _B =0	45	58	-	V
V(BR) _{EBO}	I _E =0.1mA, I _C =0	7	-	-	V
I _{CBO}	V _{CB} =35V, I _E =0	-	-	0.1	μA
I _{EBO}	V _{EB} =6V, I _C =0	-	-	0.1	μA
hFE(1)	V _{CE} =1V, I _C =100mA	160	-	320	-
hFE(2)	V _{CE} =1V, I _C =800mA	40	-	-	-
hFE(3)	V _{CE} =1V, I _C =5.0mA	45	-	-	-
V _{CE(sat)}	I _C =800mA, I _B =80mA	-	0.28	0.5	V
V _{BE(sat)}	I _C =800mA, I _B =80mA	-	0.98	1.2	V
f _T	V _{CE} =10V, I _C =50mA	100	-	-	MHz

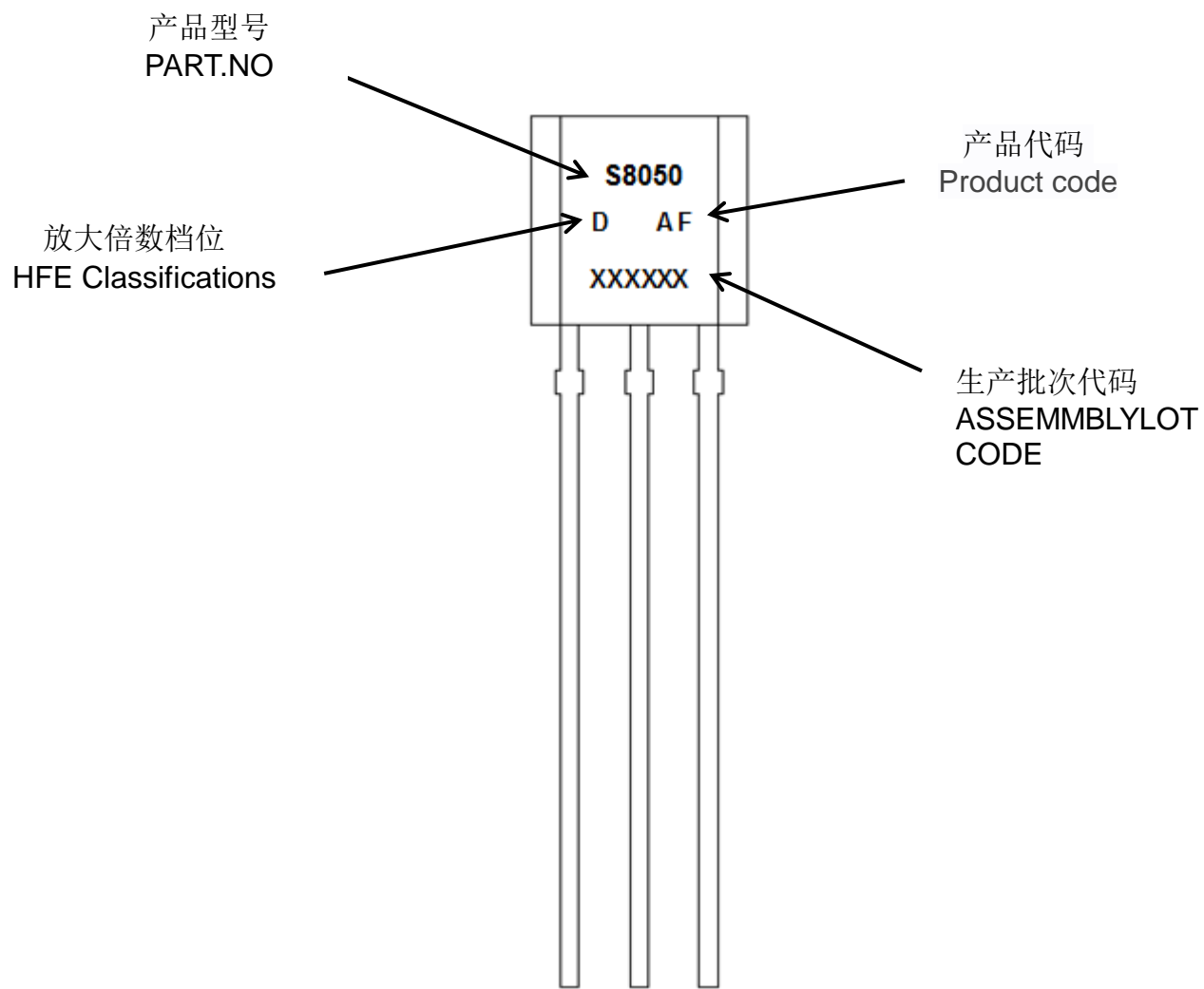
放大倍数hFE Classifications

hFE Classifications	C	D
hFE Range	120-200	160-320

典型特性曲线 **Electrical Characteristics**

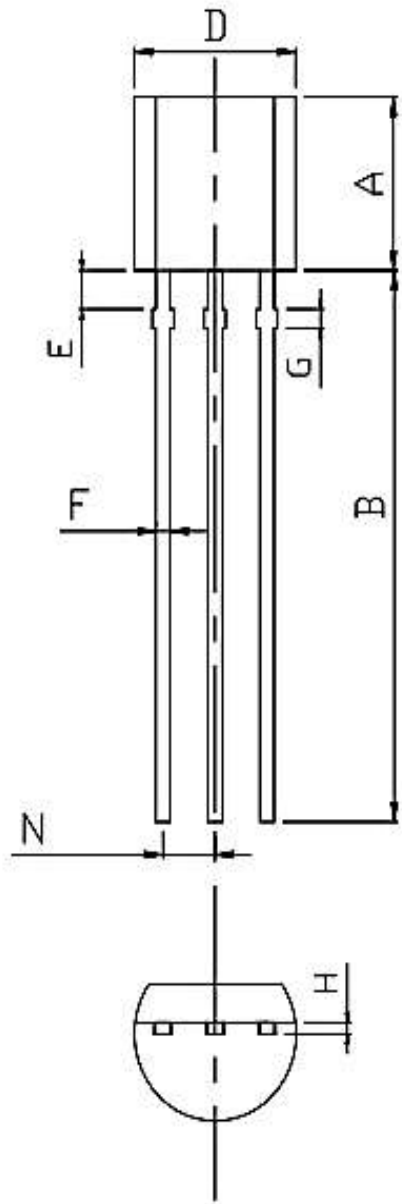


印记 Marking:



外形尺寸:
Package Dimension

T0-92



DIM	MILLIMETERS
A	4.55+0.20
B	14.50±0.30
C	3.54±0.20
D	4.56±0.20
E	1.30±0.20
F	0.46±0.20
G	0.50±0.10
H	0.32±0.10
N	1.30±0.20
P	2.52±0.20

Unit : (mm)